Marina GutiÃ©rrez

List of Publications by Year
in descending order

57 papers	705 citations	840119 11 h-index	580395 25 g-index
57 all docs	57 docs citations	57 times ranked	597 citing authors

#	Article	IF	Citations
1	Improved performance of 1.3Î¼m multilayer InAs quantum-dot lasers using a high-growth-temperature GaAs spacer layer. Applied Physics Letters, 2004, 85, 704-706.	1.5	267
2	Influences of the spacer layer growth temperature on multilayer InAsâ^•GaAs quantum dot structures. Journal of Applied Physics, 2004, 96, 1988-1992.	1.1	85
3	Improving optical properties of 1.55 Î¼m GaInNAs/GaAs multiple quantum wells with Ga(In)NAs barrier and space layer. Applied Physics Letters, 2003, 83, 4951-4953.	1.5	44
4	Influence of growth temperature on the structural and optical quality of GaInNAs/GaAs multi-quantum wells. Semiconductor Science and Technology, 2004, 19, 813-818.	1.0	20
5	Effects of alloy intermixing on the lateral confinement potential in InAsâ^•GaAs self-assembled quantum dots probed by intersublevel absorption spectroscopy. Applied Physics Letters, 2007, 90, 163107.	1.5	19
6	High quality Al2O3/(100) oxygen-terminated diamond interface for MOSFETs fabrication. Applied Physics Letters, 2018, 112, .	1.5	19
7	Direct growth of InAs/GaSb type II superlattice photodiodes on silicon substrates. IET Optoelectronics, 2018, 12, 2-4.	1.8	16
8	Determination of alumina bandgap and dielectric functions of diamond MOS by STEM-VEELS. Applied Surface Science, 2018, 461, 93-97.	3.1	16
9	Composition modulation in GaInNAs quantum wells: Comparison of experiment and theory. Journal of Applied Physics, 2005, 97, 073705.	1.1	14
10	Diamond/Î³-alumina band offset determination by XPS. Applied Surface Science, 2021, 535, 146301.	3.1	14
11	Solid solution strengthening in GaSb/GaAs: A mode to reduce the TD density through Be-doping. Applied Physics Letters, 2017, 110, .	1.5	13
12	Effect of the growth parameters on the structure and morphology of InAs/InGaAs/GaAs DWELL quantum dot structures. Journal of Crystal Growth, 2005, 278, 151-155.	0.7	11
13	2.5-Âµm InGaAs photodiodes grown on GaAs substrates by interfacial misfit array technique. Infrared Physics and Technology, 2017, 81, 320-324.	1.3	11
14	Strain interactions and defect formation in stacked InGaAs quantum dot and dot-in-well structures. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 245-251.	1.3	10
15	Optimizing the growth of 1.3-Î¼m InAs/InGaAs dots-in-a-well structure: Achievement of high-performance laser. Materials Science and Engineering C, 2005, 25, 779-783.	3.8	10
16	Structural and optical quality of InGaAsN quantum wells grown on misoriented GaAs (111)b substrates by molecular beam epitaxy. Journal of Crystal Growth, 2004, 270, 62-68.	0.7	8
17	Strain relaxation behavior of InxGa1â^'xAs quantum wells on vicinal GaAs (111)B substrates. Applied Physics Letters, 2002, 80, 1541-1543.	1.5	7
18	High-performance 1.3â€…Âµm InAs/GaAs quantum-dot lasers with low threshold current and negative characteristic temperature. IEE Proceedings: Optoelectronics, 2006, 153, 280-283.	0.8	7

#	Article	IF	Citations
19	Lasing and spontaneous emission characteristics of 1.3Î¼m In(Ga)As quantum-dot lasers. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 382-385.	1.3	6
20	Structural and optical properties of high In and N content GaInNAs quantum wells. Thin Solid Films, 2005, 483, 185-190.	0.8	6
21	Unfaulting of dislocation loops in the GaInNAs alloy: An estimation of the stacking fault energy. Journal of Applied Physics, 2005, 98, 023521.	1.1	6
22	High performance 1.3Î¼m InAs/GaAs quantum dot lasers with low threshold current and negative characteristic temperature. , 2006, 6184, 374.		6
23	Quantification of InxGa1â^'xP composition modulation by nanometric scale HAADF simulations. Applied Surface Science, 2013, 269, 138-142.	3.1	6
24	Twins and strain relaxation in zinc-blende GaAs nanowires grown on silicon. Applied Surface Science, 2017, 395, 195-199.	3.1	6
25	Impact of Nonhomoepitaxial Defects in Depleted Diamond MOS Capacitors. IEEE Transactions on Electron Devices, 2018, 65, 1830-1837.	1.6	6
26	Control of the Alumina Microstructure to Reduce Gate Leaks in Diamond MOSFETs. Nanomaterials, 2018, 8, 584.	1.9	6
27	Effect of graded buffer design on the defect structure in InGaAs/GaAs (111)B heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 27-31.	1.7	5
28	Critical barrier thickness for the formation of InGaAs/GaAs quantum dots. Materials Science and Engineering C, 2005, 25, 798-803.	3.8	5
29	An approach to the formation mechanism of the composition fluctuation in GaInNAs quantum wells. Semiconductor Science and Technology, 2005, 20, 1096-1102.	1.0	5
30	New relaxation mechanisms in InGaAs/GaAs (111) multiple quantum well. Microelectronics Journal, 1999, 30, 467-470.	1.1	4
31	Relaxation study of InxGa1â^'xAs/GaAs quantum-well structures grown by MBE on (001) and (111)B GaAs for long wavelength applications. Journal of Crystal Growth, 1999, 206, 287-293.	0.7	4
32	MPCVD Diamond Lateral Growth Through Microterraces to Reduce Threading Dislocations Density. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700242.	0.8	4
33	GaSb and GaSb/AlSb Superlattice Buffer Layers for High-Quality Photodiodes Grown on Commercial GaAs and Si Substrates. Journal of Electronic Materials, 2018, 47, 5083-5086.	1.0	4
34	Interfacial integrity enhancement of atomic layer deposited alumina on boron doped diamond by surface plasma functionalization. Surface and Coatings Technology, 2020, 397, 125991.	2.2	4
35	Cathodoluminescence study of pyramidal facets in piezoelectric InGaAs/GaAs multiple quantum well pin photodiodes. Microelectronics Journal, 1999, 30, 427-431.	1.1	3
36	Optical properties of InxGa1â^'xAs/GaAs MQW structures on (111)B GaAs grown by MBE: dependence on substrate miscut. Journal of Crystal Growth, 1999, 201-202, 1085-1088.	0.7	3

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37	Influence of substrate misorientation on the structural characteristics of InGaAs/GaAs MQW on (111)B GaAs grown by MBE. Thin Solid Films, 1999, 343-344, 558-561.	0.8	3
38	Structural defects characterisation of GaInNAs MQWs by TEM and PL. IEE Proceedings: Optoelectronics, 2004, 151, 385-388.	0.8	3
39	Proton radiation effect on InAs avalanche photodiodes. Optics Express, 2017, 25, 2818.	1.7	3
40	Relaxation study of AlGaAs cladding layers in InGaAs/GaAs (111)B lasers designed for 1.0â€"1.1Î¼m operation. Microelectronics Journal, 2002, 33, 553-557.	1.1	2
41	Investigations of 1.55-Î¼m GaInNAs/GaAs heterostructures by optical spectroscopy. IEE Proceedings: Optoelectronics, 2004, 151, 331-334.	0.8	2
42	Improvement in the optical quality of GaInNAs/GaInAs quantum well structures by interfacial strain reduction. IEE Proceedings: Optoelectronics, 2004, 151, 301-304.	0.8	2
43	Growth and characterization of multiple layer quantum dot lasers. , 2005, , .		2
44	InAs/GaAs quantum dots morphology: Nanometric scale HAADF simulations. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 88-93.	1.7	2
45	Influence of substrate misorientation on the optical and structural properties of InGaAs/GaAs single strained quantum wells grown on (111)B GaAs by molecular beam epitaxy. Microelectronics Journal, 1999, 30, 373-378.	1.1	1
46	Influence of structure and defects on the performance of dot-in-well laser structures. , 2005, , .		1
47	Characterization of structure and defects in dot-in-well laser structures. Materials Science and Engineering C, 2005, 25, 793-797.	3.8	1
48	Composition modulation analysis of InxGa1â^'xP layers grown on (001) germanium substrates. Applied Surface Science, 2010, 256, 5681-5683.	3.1	1
49	Analysis by HR-STEM of the Strain Generation in InP after SiNx Deposition and ICP Etching. Journal of Electronic Materials, 2020, 49, 5226-5231.	1.0	1
50	Study of Early Stages in the Growth of Boronâ€Doped Diamond on Carbon Fibers. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000284.	0.8	1
51	The role of climb and glide in misfit relief of InGaAs/GaAs(111)B heterostructures. Microelectronics Journal, 2002, 33, 559-563.	1.1	0
52	Composition fluctuations in GaInNAs multi-quantum wells. IEE Proceedings: Optoelectronics, 2004, 151, 271-274.	0.8	0
53	Spinodal decomposition in GaInNAs/GaAs multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1292-1297.	0.8	0
54	Growth and Characterization of 1.3Î¼m Multi-Layer Quantum Dots Lasers Incorporating High Growth Temperature Spacer Layers. AIP Conference Proceedings, 2005, , .	0.3	0

#	Article	IF	Citations
55	Silicon (001) Heteroepitaxy on 3C-SiC(001)/Si(001) Seed. Materials Science Forum, 2018, 924, 128-131.	0.3	0
56	How to Grow Fully (100) Oriented SiC/Si/SiC/Si Multiâ€Stack. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800588.	0.8	0
57	Activation energy for surface diffusion in GaInNAs quantum wells. , 0, , 279-282.		0